



STN2NF10

N-CHANNEL 100V - 0.23Ω - 2A SOT-223 STripFET™ II POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STN2NF10	100 V	< 0.26 Ω	2 A

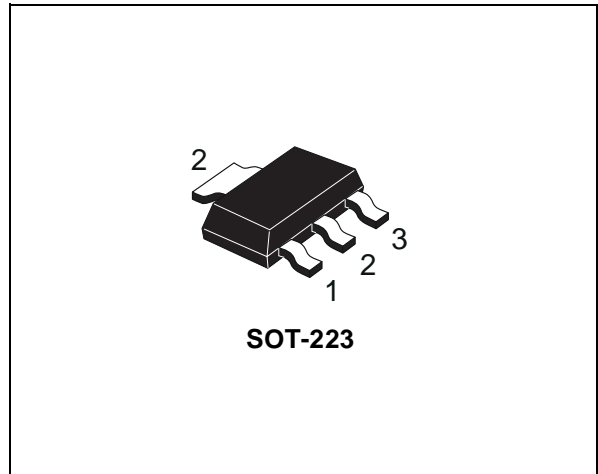
- TYPICAL R_{DS(on)} = 0.23 Ω

DESCRIPTION

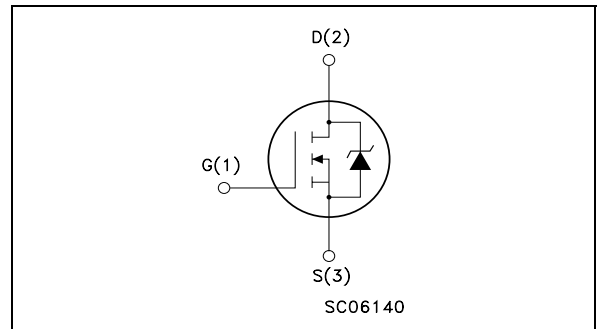
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- DC-DC & DC-AC CONVERTERS
- DC MOTOR CONTROL (DISK DRIVERS, etc.)
- SYNCHRONOUS RECTIFICATION



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	100	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	100	V
V _{GS}	Gate- source Voltage	± 20	V
I _{D(●)}	Drain Current (continuous) at T _C = 25°C	2	A
I _D	Drain Current (continuous) at T _C = 100°C	1.26	A
I _{DM(●●)}	Drain Current (pulsed)	8	A
P _{tot}	Total Dissipation at T _C = 25°C	2.5	W
	Derating Factor	0.02	W/°C
E _{AS(1)}	Single Pulse Avalanche Energy	300	mJ
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(●●) Pulse width limited by safe operating area.
(●) Current limited by the package

(1) I_{SD} ≤ 1A, di/dt ≤ 300A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

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THERMAL DATA

Rthj-pcb	Thermal Resistance Junction-PCB (1 inch ² copper board)		50	°C/W
Rthj-pcb T _I	Thermal Resistance Junction-PCB (min. footprint) Maximum Lead Temperature For Soldering Purpose	Typ	90 260	°C/W °C

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	100			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2		4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 1 A		0.23	0.26	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 1A		2.5		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		280		pF
C _{oss}	Output Capacitance			45		pF
C _{riss}	Reverse Transfer Capacitance			20		pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 50\text{ V}$ $I_D = 1\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 1)		6 10		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 80\text{ V}$ $I_D = 2\text{ A}$ $V_{GS} = 10\text{ V}$ (see test circuit, Figure 2)		10 2.5 4		nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f t_c	Turn-off Delay Time Fall Time Cross-over Time	$V_{clamp} = 80\text{ V}$ $I_D = 2\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$		19 4 15		ns ns ns

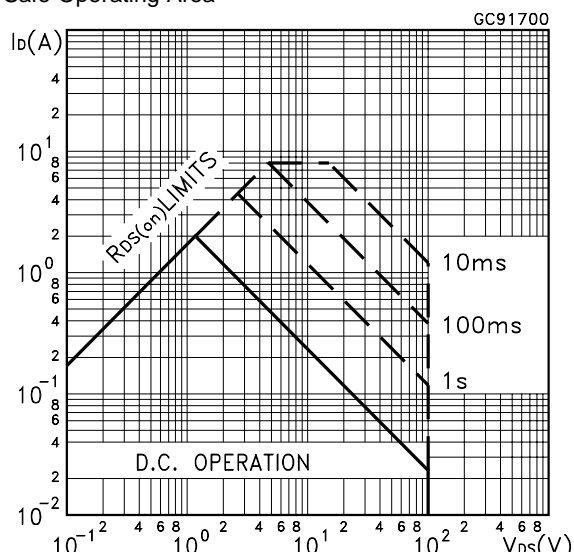
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				2 8	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 2\text{ A}$ $V_{GS} = 0$			1.2	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 2\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 10\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 3)		70 175 5		ns nC A

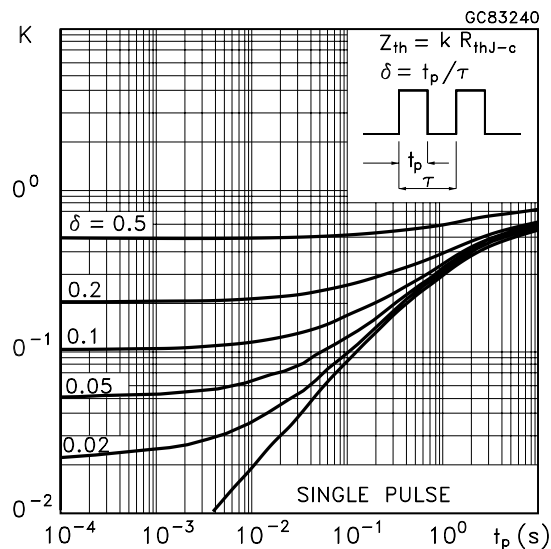
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

(\bullet) Pulse width limited by safe operating area.

Safe Operating Area

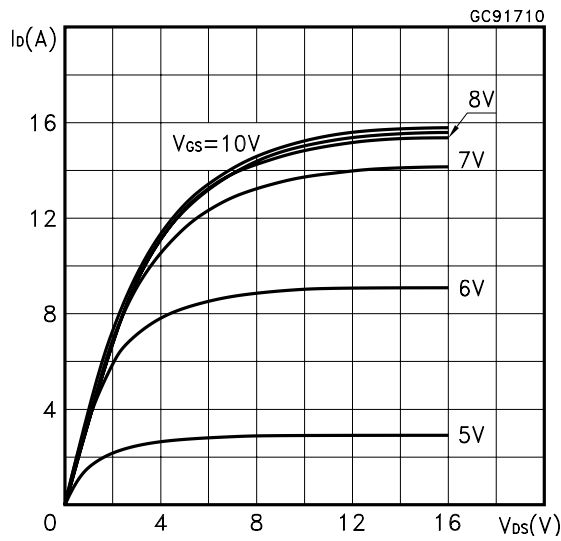


Thermal Impedance

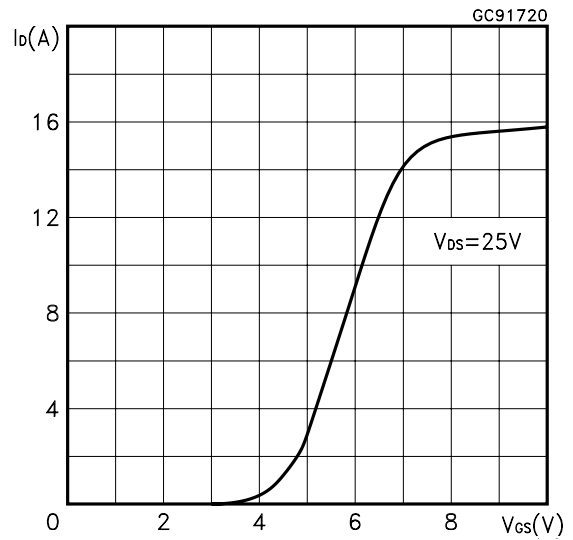


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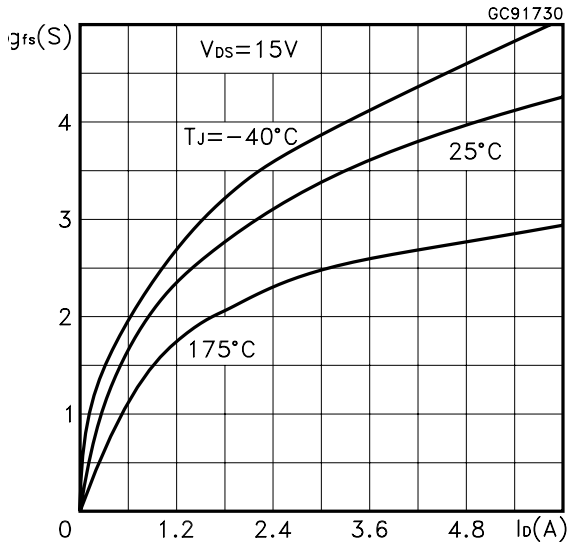
Output Characteristics



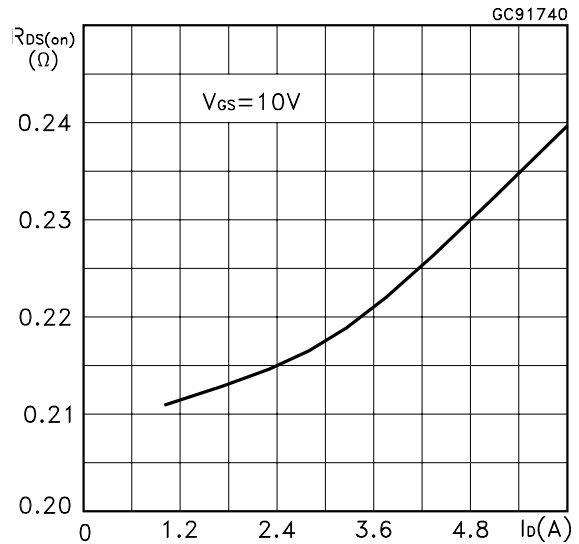
Transfer Characteristics



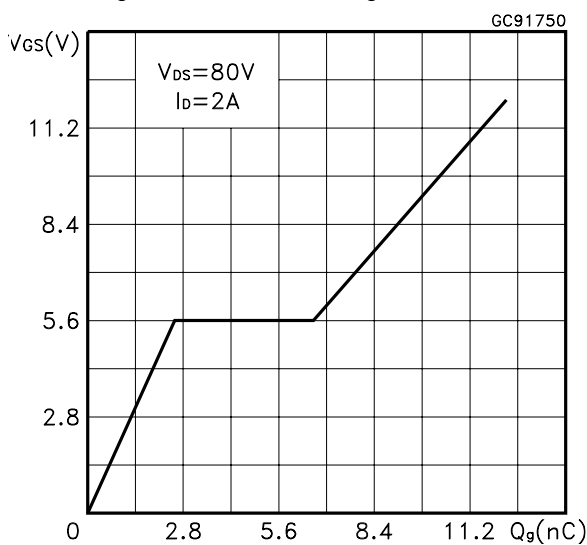
Transconductance



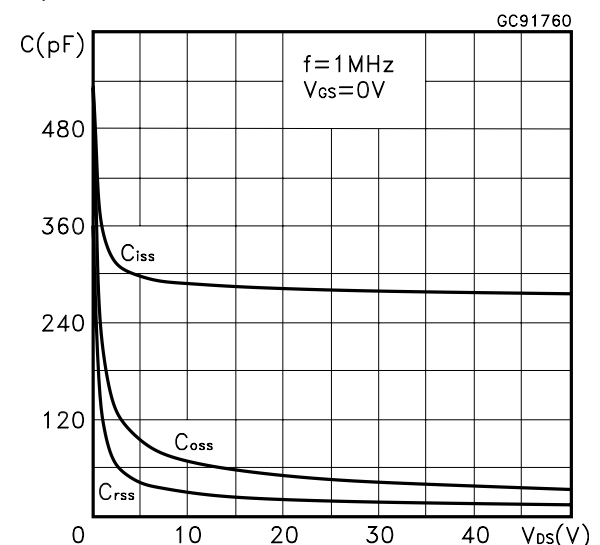
Static Drain-source On Resistance



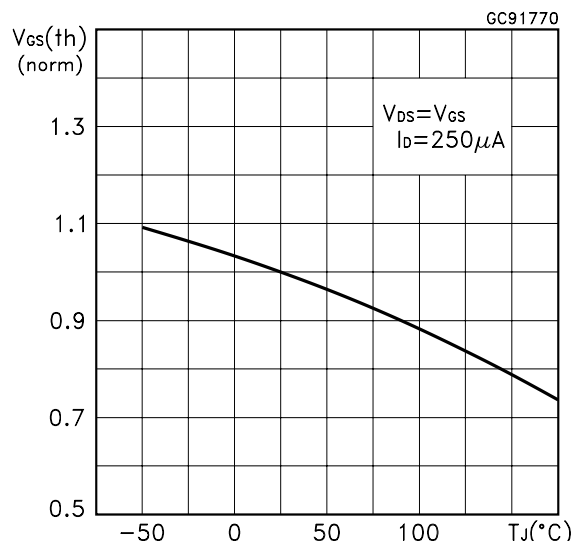
Gate Charge vs Gate-source Voltage



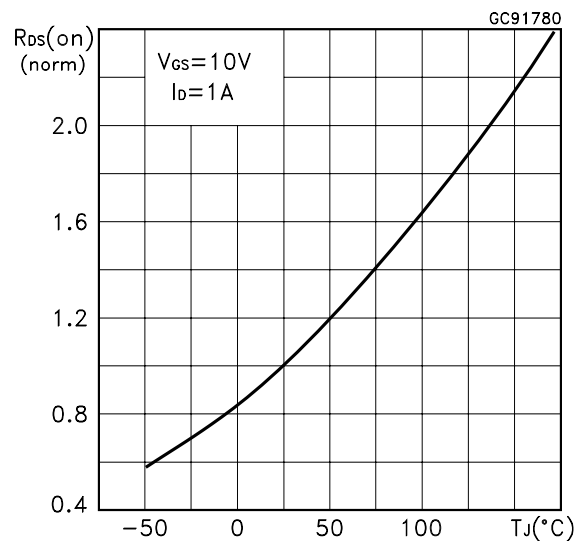
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics

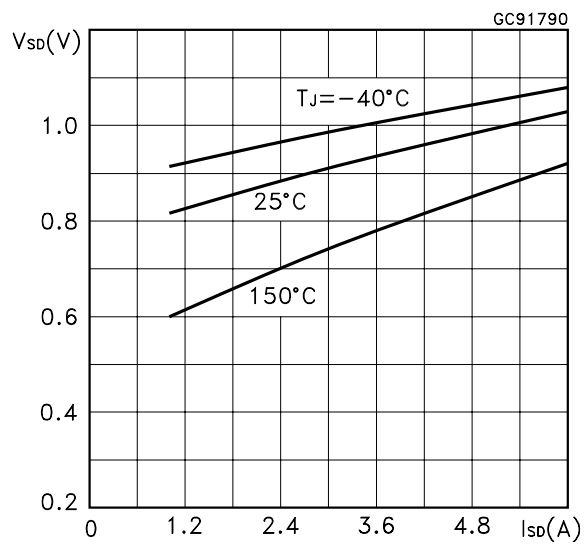


Fig. 1: Switching Times Test Circuits For Resistive Load

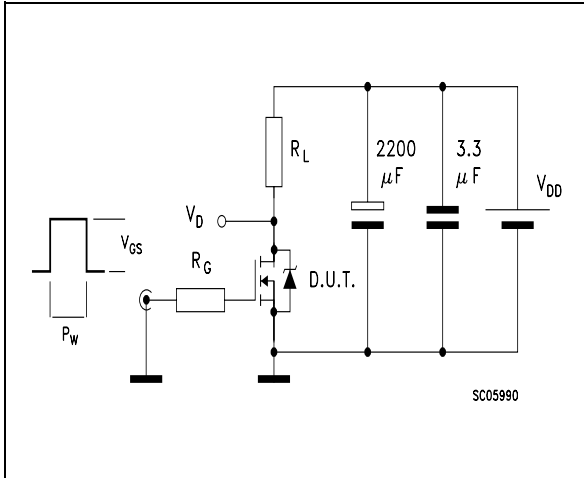


Fig. 2: Gate Charge test Circuit

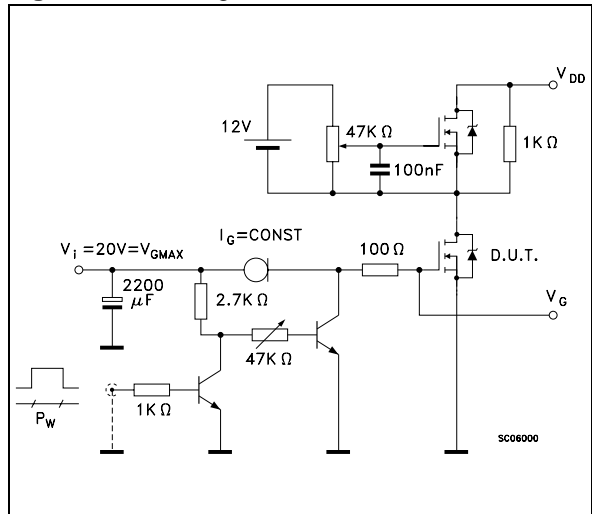
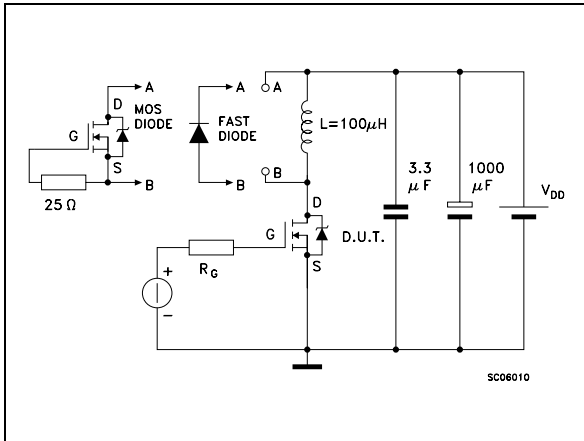
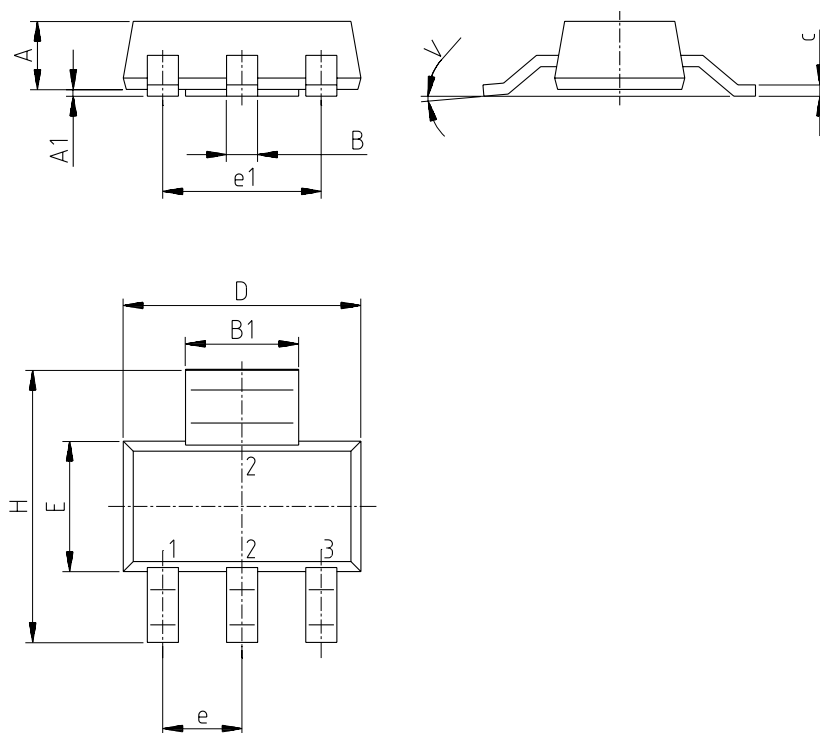


Fig. 3: Test Circuit For Diode Recovery Behaviour



SOT-223 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.80			0.071
B	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
c	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
e		2.30			0.090	
e1		4.60			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V			10°			10°
A1		0.02				



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